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L11: Entry 44 of 51

File: DWPI

Jul 1, 1991

DERWENT-ACC-NO: 1991-234547

DERWENT-WEEK: 199132

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TITLE: Growing single-crystal silicon carbide layer on silicon wafer - by depositing silicon layer on carbonised wafer surface, and heating in hydrocarbon atmos. NoAbstract Dwg 1,2/2

PATENT-ASSIGNEE: FUJITSU LTD (FUIT)

PRIORITY-DATA: 1989JP-0292903 (November 10, 1989)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
JP 03153023 A	July 1, 1991		000	

APPLICATION-DATA:

PUB-NO	APPL-DATE	APPL-NO	DESCRIPTOR
JP03153023A	November 10, 1989	1989JP-0292903	

INT-CL (IPC): H01L 21/20

DERWENT-CLASS: L03 U11

CPI-CODES: L04-A; L04-A01; L04-C16;

EPI-CODES: U11-C01A9; U11-C01J4; U11-C03J7;

57.6 208

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U-S PATENT

J: